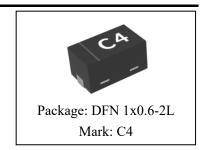


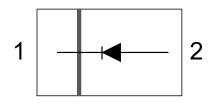
YVC032P034R-C4

Hyperabrupt Junction Tuning Varactor

Features

- High capacitance ratio: $C_{0V} / C_{5V} = 3.4$ (typ.)
- Designed for high-volume, low-cost battery applications
- Available lead (Pb)-free and RoHS-compliant MSL-1 @ 260°C per JEDEC J-STD-020
- Available in tape and reel packaging
- Industry Standard DFN1x0.6-2L Package





Functional Block Diagram

Product Description

The YVC032P034R device is GaAs hyperabrupt junction varactor diodes specifically designed for VCOs applications, The specified high capacitance ratio and low R_s of YVC032P034R make it attractive for low phase noise VCOs in wireless systems up to and beyond 3.5GHz. Applications include low-noise and wideband UHF and VHF VCO for GSM, PCS, CDMA and analog phones.

Absolute Maximum Ratings

| Characteristic | Rating | Unit |
|--|-------------|------|
| Forward current (I _F) | 20 | mA |
| Power dissipation (P _D) | 250 | mW |
| Storage temperature (T _{ST}) | -55 to +150 | °C |
| Operating temperature (Top) | -55 to +125 | °C |
| ESD human body model | Class1A | |



Caution!

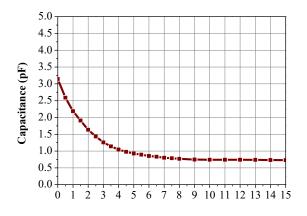
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

Electrical Specifications@25 $\mathcal C$

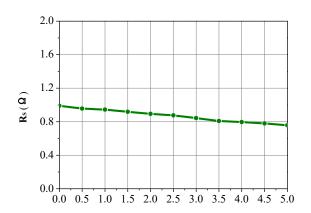
| Parameter | Condition | Specification | | | Unit |
|--------------------------------------|---|---------------|------|------|-------|
| | | Min. | Тур. | Max. | Offic |
| Reverse Current (I _R) | V _R = 15 V | | | 20 | nA |
| Capacitance (C _T) | C_T @ 0.5 V, V_R = 0.5 V, F = 1 MHz | | 2.59 | | pF |
| Capacitance (C _T) | C_T @ 5 V, V_R = 5 V, F = 1 MHz | | 0.93 | | pF |
| Capacitance Ratio (CTR) | C _T (0.5 V)/C _T (5 V) | | 2.78 | | |
| Series Resistance (Rs) | V _R = 1 V, F = 100 MHz | | | 0.94 | Ω |
| Breakdown Voltage (V _{BR}) | I _R = 10 μA | 20 | | | V |



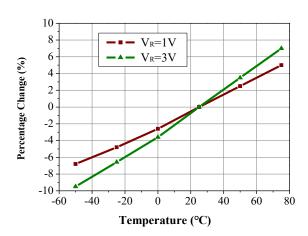
Typical Performance Data



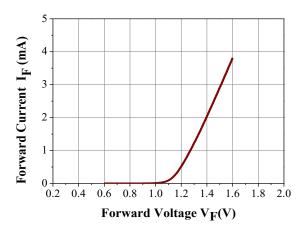
Capacitance vs. Reverse Voltage



Series Resistance vs. Reverse Voltage @ 100 MHz



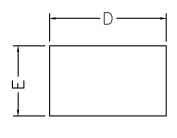
Relative Capacitance Change vs. Temperature



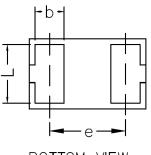
Forward I-V characteristic curve

Package Diagram

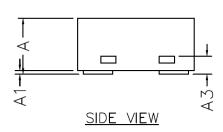
(Units: millimeters)



TOP VIEW



BOTTOM VIEW



| COMMON DIMENSIONS(MM) | | | | | |
|-----------------------|------------------|------|------|--|--|
| PKG. | X1: EXTREME THIN | | | | |
| REF. | MIN. | NOM. | MAX | | |
| Α | >0.4 | _ | 0.50 | | |
| A1 | 0.00 | _ | 0.05 | | |
| А3 | 0.125REF. | | | | |
| D | 0.95 | 1.00 | 1.05 | | |
| E | 0.55 | 0.60 | 0.65 | | |
| b | 0.20 | 0.25 | 0.30 | | |
| L | 0.45 | 0.50 | 0.55 | | |
| | _ | _ | _ | | |
| | _ | _ | _ | | |
| е | 0.65 BSC | | | | |

Part Number Naming Conventions:

(e.g.) Y VC 032 P 034 R - C4

- ① Company: INNOTION
- ② Product ID: (**VC**=Variable Capacitance Diode)
- ③ Capacitance (C_T)@V_R=0V is expressed by three-digit alphanumeric (e.g. **032**=3.2pF, **228**=22.8pF)
- ④ Capacitance Unit: pF
- \bigcirc Capacitance ratio: C_{0V} / C_{5V} is expressed by three-digit alphanumeric (e.g. **034** is C_{0V} / C_{5V} =3.4)
- 6 Ratio
- ⑦ Internal part number